

# MITSUBISHI RF POWER TRANSISTOR 2SC2630

## NPN EPITAXIAL PLANAR TYPE

### DESCRIPTION

2SC2630 is a silicon NPN epitaxial planar type transistor designed for RF power amplifiers in VHF band mobile radio applications.

### FEATURES

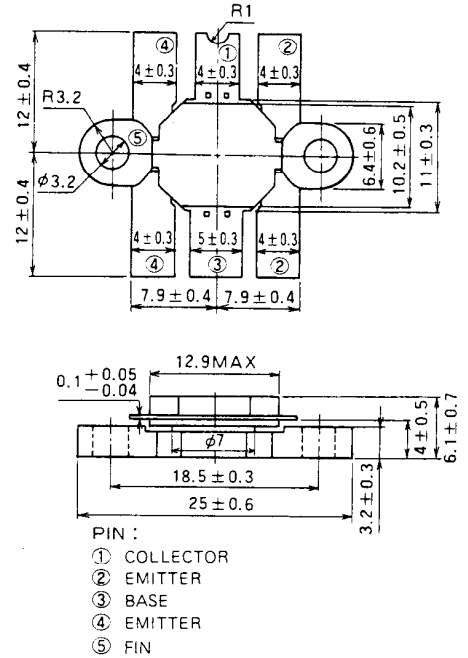
- High power gain:  $G_{pe} \geq 7\text{dB}$   
@  $V_{CC} = 12.5\text{V}$ ,  $P_O = 50\text{W}$ ,  $f = 175\text{MHz}$
- Emitter ballasted construction and gold metallization for high reliability and good performances.
- Low thermal resistance ceramic package with flange.
- Ability of withstanding more than 20:1 load VSWR when operated at  $V_{CC} = 15.2\text{V}$ ,  $P_O = 50\text{W}$ ,  $f = 175\text{MHz}$ ,  $T_C = 25^\circ\text{C}$ .
- Equivalent input/output series impedance:  
 $Z_{in} = 0.8 + j1.2\Omega$  @  $P_O = 60\text{W}$ ,  $V_{CC} = 12.5\text{V}$ ,  $f = 175\text{MHz}$   
 $Z_{out} = 1.5 - j0.6\Omega$

### APPLICATION

40 to 60 watts output power amplifiers in VHF band mobile radio applications.

### OUTLINE DRAWING

Dimensions in mm



- PIN :
- ① COLLECTOR
  - ② EMITTER
  - ③ BASE
  - ④ EMITTER
  - ⑤ FIN

NOTE: ALL ELECTRODES ARE ISOLATED FROM FLANGE.

T-40

### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Ratings	Unit
$V_{CB0}$	Collector to base voltage		35	V
$V_{EB0}$	Emitter to base voltage		4	V
$V_{CE0}$	Collector to emitter voltage	$R_{BE} = \infty$	17	V
$I_C$	Collector current		14	A
$P_C$	Collector dissipation	$T_a = 25^\circ\text{C}$	5.5	W
		$T_C = 25^\circ\text{C}$	100	
$T_j$	Junction temperature		175	$^\circ\text{C}$
$T_{stg}$	Storage temperature		-55 to 175	$^\circ\text{C}$
$R_{th-a}$	Thermal resistance	Junction to ambient	27.2	$^\circ\text{C/W}$
$R_{th-c}$		Junction to case	1.5	$^\circ\text{C/W}$

Note: Above parameters are guaranteed independently.

### ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
$V_{(BR)EBO}$	Emitter to base breakdown voltage	$I_E = 10\text{mA}$ , $I_C = 0$	4			V
$V_{(BR)CBO}$	Collector to base breakdown voltage	$I_C = 10\text{mA}$ , $I_E = 0$	35			V
$V_{(BR)CEO}$	Collector to emitter breakdown voltage	$I_C = 0.1\text{A}$ , $R_{BE} = \infty$	17			V
$I_{CBO}$	Collector cutoff current	$V_{CB} = 15\text{V}$ , $I_E = 0$			5	mA
$I_{EBO}$	Emitter cutoff current	$V_{EB} = 3\text{V}$ , $I_C = 0$			5	mA
$h_{FE}$	DC forward current gain *	$V_{CE} = 10\text{V}$ , $I_C = 0.2\text{A}$	10	40	180	—
$P_O$	Output power	$V_{CC} = 12.5\text{V}$ , $P_{in} = 10\text{W}$ , $f = 175\text{MHz}$	50	60		W
$\eta_C$	Collector efficiency		60	70		%

Note: \* Pulse test,  $P_w = 150\mu\text{s}$ , duty = 5%.

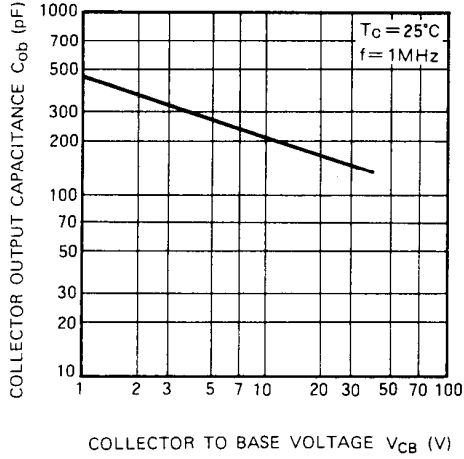
Above parameters, ratings, limits and conditions are subject to change.

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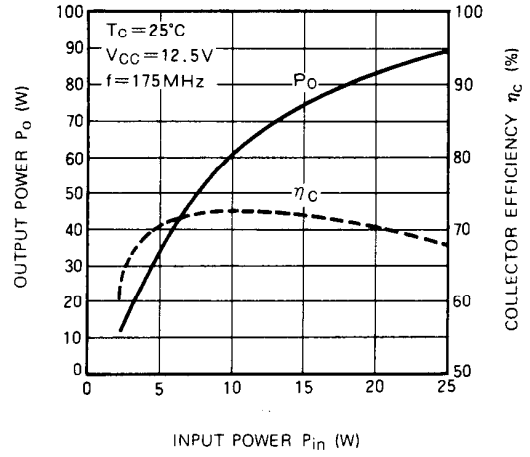


**NPN EPITAXIAL PLANAR TYPE**

**COLLECTOR OUTPUT CAPACITANCE VS. COLLECTOR TO BASE VOLTAGE**



**OUTPUT POWER, COLLECTOR EFFICIENCY VS. INPUT POWER**



**OUTPUT POWER VS. COLLECTOR SUPPLY VOLTAGE**

